

SEMICONDUCTOR DEVICE HAVING A PAD METAL LAYER AND A LOWER METAL LAYER THAT ARE ELECTRICALLY COUPLED, WHEREAS APERTURES ARE FORMED IN THE LOWER METAL LAYER BELOW A CENTER AREA OF THE PAD METAL LAYER

5 ABSTRACT OF THE INVENTION

A semiconductor device is disclosed and provided. The semiconductor device includes a pad metal layer having a perimeter area and a center area. Further, the semiconductor device has a lower metal layer having a plurality of apertures below the center area of the pad metal layer. Moreover, an interlayer dielectric is formed between the pad metal layer and the lower metal layer. In an
10 embodiment, the semiconductor device also includes a plurality of vias formed in the interlayer dielectric. The vias electrically couple the pad metal layer and the lower metal layer. Additionally, the vias are located below the perimeter area of the pad metal layer.